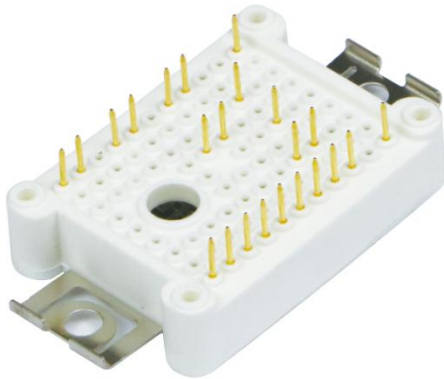




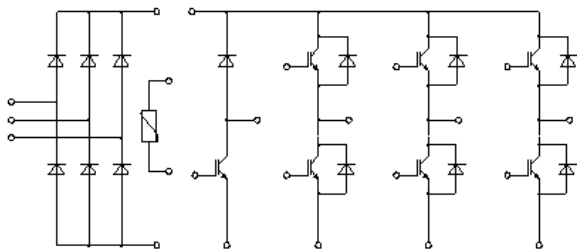
IGBT Modules

V_{CES}	1200V
I_C	10A

Applications

- Motor Drivers
- AC and DC Servo Drive Amplifier
- UPS (Uninterruptible Power Supplies)

Circuit



Features

- Low switching losses
- Low $V_{CE(sat)}$ with positive temperature coefficient
- Including fast & soft recovery anti-parallel FWD
- Low inductance case
- High short circuit capability(10us)
- Isolated heatsink using DBC technology
- Maximum junction temperature 175℃

● IGBT- inverter

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Collector-Emitter Voltage	V_{CES}	$V_{GE}=0V, I_C=1mA, T_{vj}=25^{\circ}C$	1200	V
Continuous Collector Current	I_C	$T_C=100^{\circ}C, T_{vjmax}=175^{\circ}C$	10	A
Repetitive Peak Collector Current	I_{CRM}	$t_p=1ms$	20	A
Gate-Emitter Voltage	V_{GES}	$T_{vj}=25^{\circ}C$	± 20	V
Total Power Dissipation	P_{tot}	$T_C=25^{\circ}C$ $T_{vjmax}=175^{\circ}C$	100	W



● IGBT- inverter

Characteristic values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Gate-Emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}$, $I_C=0.5mA$, $T_{vj}=25^{\circ}C$	5.2	5.8	6.5	V
Collector-Emitter Cut-off Current	I_{CES}	$V_{CE}=1200V$, $V_{GE}=0V$, $T_{vj}=25^{\circ}C$			1.0	mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=10A$, $V_{GE}=15V$, $T_{vj}=25^{\circ}C$		1.80	2.50	V
		$I_C=10A$, $V_{GE}=15V$, $T_{vj}=125^{\circ}C$		1.95		
		$I_C=10A$, $V_{GE}=15V$, $T_{vj}=150^{\circ}C$		2.00		
Gate Charge	Q_G			0.13		uC
Input Capacitance	C_{ies}	$V_{CE}=25V$, $V_{GE}=0V$, $f=1MHz$, $T_{vj}=25^{\circ}C$		0.681		nF
Reverse Transfer Capacitance	C_{res}			0.023		nF
Gate-Emitter leakage current	I_{GES}	$V_{CE}=0V$, $V_{GE}=20V$, $T_{vj}=25^{\circ}C$			400	nA
Turn-on Delay Time	$t_{d(on)}$	$I_C=10A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=51\Omega$ $T_{vj}=25^{\circ}C$		76		ns
Rise Time	t_r			31		ns
Turn-off Delay Time	$t_{d(off)}$			100		ns
Fall Time	t_f			337		ns
Energy Dissipation During Turn-on Time	E_{on}			1.16		mJ
Energy Dissipation During Turn-off Time	E_{off}			0.78		mJ
Turn-on Delay Time	$t_{d(on)}$	$I_C=10A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=51\Omega$ $T_{vj}=150^{\circ}C$		74		ns
Rise Time	t_r			34		ns
Turn-off Delay Time	$t_{d(off)}$			104		ns
Fall Time	t_f			406		ns
Energy Dissipation During Turn-on Time	E_{on}			1.35		mJ
Energy Dissipation During Turn-off Time	E_{off}			0.91		mJ
SC Data	I_{SC}	$t_p \leq 10\mu s$, $V_{GE}=15V$, $T_{vj}=150^{\circ}C$, $V_{CC}=900V$, $V_{CEM} \leq 1200V$		40		A



● Diode-inverter

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	$T_{vj}=25^{\circ}\text{C}$	1200	V
Continuous DC Forward Current	I_F		10	A
Repetitive Peak Forward Current	I_{FRM}	$t_p=1\text{ms}$	20	A
I^2t -value	I^2t	$V_R=0\text{V}, t_p=10\text{ms}, T_{vj}=125^{\circ}\text{C}$	16.0	A^2s
		$V_R=0\text{V}, t_p=10\text{ms}, T_{vj}=150^{\circ}\text{C}$	14.0	

Characteristic Values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Forward Voltage	V_F	$I_F=10\text{A}, T_{vj}=25^{\circ}\text{C}$		2.00	2.80	V
		$I_F=10\text{A}, T_{vj}=125^{\circ}\text{C}$		1.85		
		$I_F=10\text{A}, T_{vj}=150^{\circ}\text{C}$		1.80		
Recovered Charge	Q_{rr}	$I_F=10\text{A}$		0.261		μC
Peak Reverse Recovery Current	I_{rr}	$V_R=600\text{V}$ $-di_F/dt=500\text{A}/\mu\text{s}$		11		A
Reverse Recovery Energy	E_{rec}	$T_{vj}=25^{\circ}\text{C}$		0.28		mJ
Recovered Charge	Q_{rr}	$I_F=10\text{A}$		0.367		μC
Peak Reverse Recovery Current	I_{rr}	$V_R=600\text{V}$ $-di_F/dt=500\text{A}/\mu\text{s}$		12		A
Reverse Recovery Energy	E_{rec}	$T_{vj}=150^{\circ}\text{C}$		0.65		mJ



● IGBT-brake-chopper

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Collector-Emitter Voltage	V_{CES}	$V_{GE}=0V, I_C=1mA, T_{vj}=25^{\circ}C$	1200	V
Continuous Collector Current	I_C	$T_C=100^{\circ}C, T_{vjmax}=175^{\circ}C$	10	A
Repetitive Peak Collector Current	I_{CRM}	$t_p=1ms$	20	A
Gate-Emitter Voltage	V_{GES}	$T_{vj}=25^{\circ}C$	± 20	V
Total Power Dissipation	P_{tot}	$T_C=25^{\circ}C, T_{vjmax}=175^{\circ}C$	100	W

Characteristic Values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Gate-emitter Threshold Voltage	$V_{GE(th)}$	$V_{GE}=V_{CE}, I_C=0.5mA, T_{vj}=25^{\circ}C$	5.2	5.8	6.5	V
Collector-Emitter Cut-off Current	I_{CES}	$V_{CE}=1200V, V_{GE}=0V, T_{vj}=25^{\circ}C$			1.0	mA
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=10A, V_{GE}=15V, T_{vj}=25^{\circ}C$		1.80	2.50	V
		$I_C=10A, V_{GE}=15V, T_{vj}=125^{\circ}C$		1.95		
		$I_C=10A, V_{GE}=15V, T_{vj}=150^{\circ}C$		2.00		
Gate Charge	Q_G			0.13		uC
Input Capacitance	C_{ies}	$V_{CE}=25V, V_{GE}=0V$ $f=1MHz, T_{vj}=25^{\circ}C$		0.681		nF
Reverse Transfer Capacitance	C_{res}			0.023		nF
Gate-Emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^{\circ}C$			400	nA
Turn-on Delay Time	$t_{d(on)}$	$I_C=10A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=51\Omega$ $T_{vj}=25^{\circ}C$		76		ns
Rise Time	t_r			31		ns
Turn-off Delay Time	$t_{d(off)}$			100		ns
Fall Time	t_f			337		ns
Energy Dissipation During Turn-on Time	E_{on}			1.16		mJ
Energy Dissipation During Turn-off Time	E_{off}			0.78		mJ



Turn-on Delay Time	$t_{d(on)}$	$I_C=10A$ $V_{CE}=600V$ $V_{GE}=\pm 15V$ $R_G=51\Omega$ $T_{vj}=150^\circ C$		74		ns
Rise Time	t_r			34		ns
Turn-off Delay Time	$t_{d(off)}$			104		ns
Fall Time	t_f			406		ns
Energy Dissipation During Turn-on Time	E_{on}			1.35		mJ
Energy Dissipation During Turn-off Time	E_{off}			0.91		mJ
SC Data	I_{SC}	$t_p \leq 10\mu s, V_{GE}=15V, T_{vj}=150^\circ C$ $V_{CC}=900V, V_{CEM} \leq 1200V$		40		A

● Diode-brake-chopper

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	$T_{vj}=25^\circ C$	1200	V
Continuous DC Forward Current	I_F		10	A
Repetitive Peak Forward Current	I_{FRM}	$t_p=1ms$	20	A
I^2t -value	I^2t	$V_R=0V, t_p=10ms, T_{vj}=125^\circ C$	16.0	A ² s
		$V_R=0V, t_p=10ms, T_{vj}=150^\circ C$	14.0	

Characteristic Values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Forward Voltage	V_F	$I_F=10A, T_{vj}=25^\circ C$		2.00		V
		$I_F=10A, T_{vj}=125^\circ C$		1.85		
		$I_F=10A, T_{vj}=150^\circ C$		1.80		
Recovered Charge	Q_{rr}	$I_F=10A$		0.261		μC
Peak Reverse Recovery Current	I_{rr}	$V_R=600V$ $-di_F/dt=500A/\mu s$		11		A
Reverse Recovery Energy	E_{rec}	$T_{vj}=25^\circ C$		0.28		mJ
Recovered Charge	Q_{rr}	$I_F=10A$		0.367		μC
Peak Reverse Recovery Current	I_{rr}	$V_R=600V$ $-di_F/dt=500A/\mu s$		12		A
Reverse Recovery Energy	E_{rec}	$T_{vj}=150^\circ C$		0.65		mJ



● Diode-rectifier

Absolute Maximum Ratings

Parameter	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	$T_{vj}=25^{\circ}\text{C}$	1600	V
Average output Current 50/60Hz, sine wave	$I_{F(AV)}$	$T_C=100^{\circ}\text{C}$	10	A
Maximum RMS Current at Rectifier Output	I_{RMSM}	$T_C=100^{\circ}\text{C}$	10	A
Surge Forward Current	I_{FSM}	$V_R=0\text{V}, t_p=10\text{ms}, T_{vj}=25^{\circ}\text{C}$	290	A
		$V_R=0\text{V}, t_p=10\text{ms}, T_{vj}=150^{\circ}\text{C}$	230	A
I^2t -value	I^2t	$V_R=0\text{V}, t_p=10\text{ms}, T_{vj}=25^{\circ}\text{C}$	400	A^2s
		$V_R=0\text{V}, t_p=10\text{ms}, T_{vj}=150^{\circ}\text{C}$	260	A^2s

Characteristic Values

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Diode Forward Voltage	V_F	$I_F=10\text{A}, T_{vj}=150^{\circ}\text{C}$		1.00		V
Reverse Current	I_R	$T_{vj}=150^{\circ}\text{C}, V_R=1600\text{V}$			1.0	mA

● NTC Thermistor

Characteristic Values

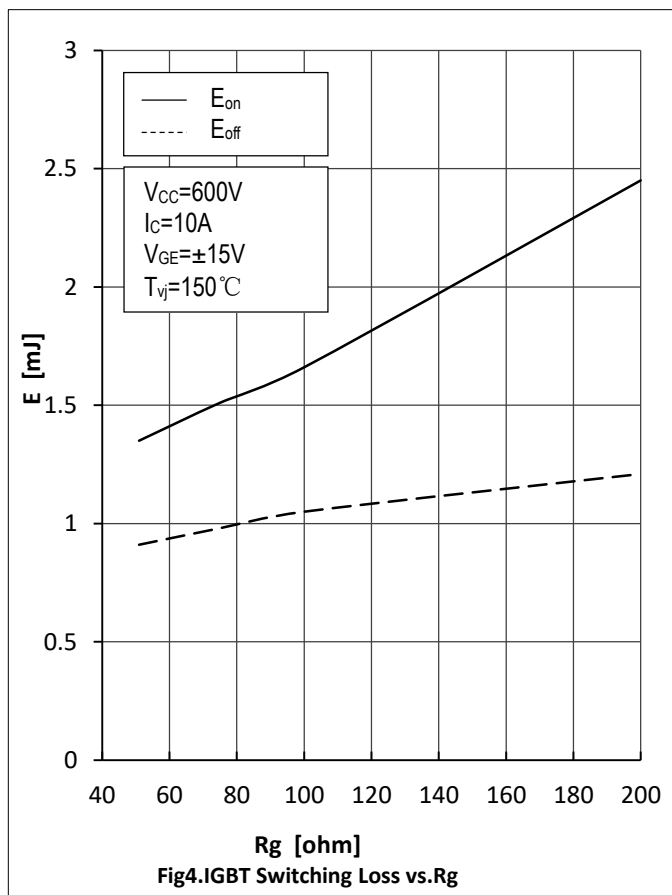
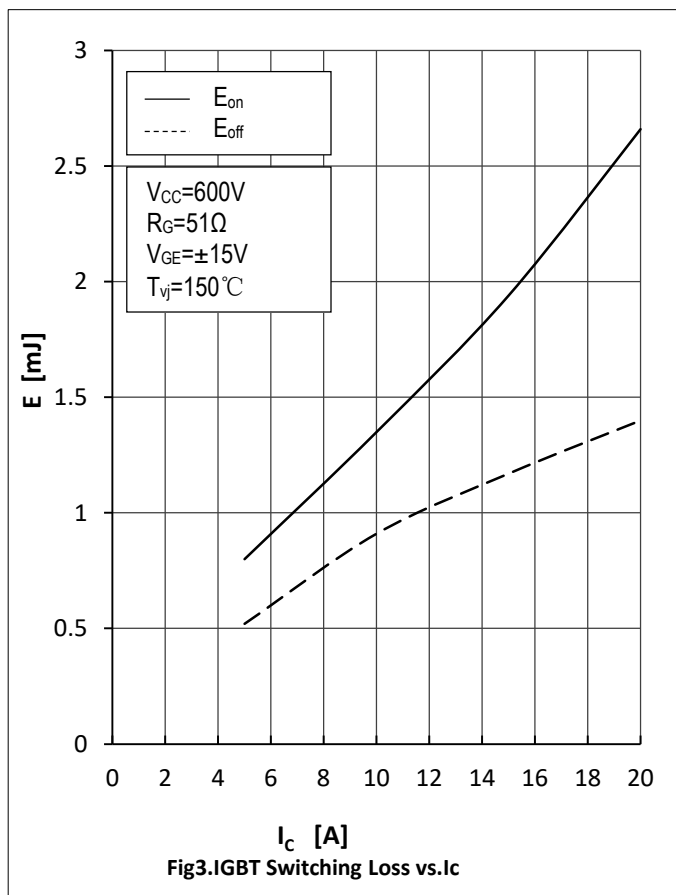
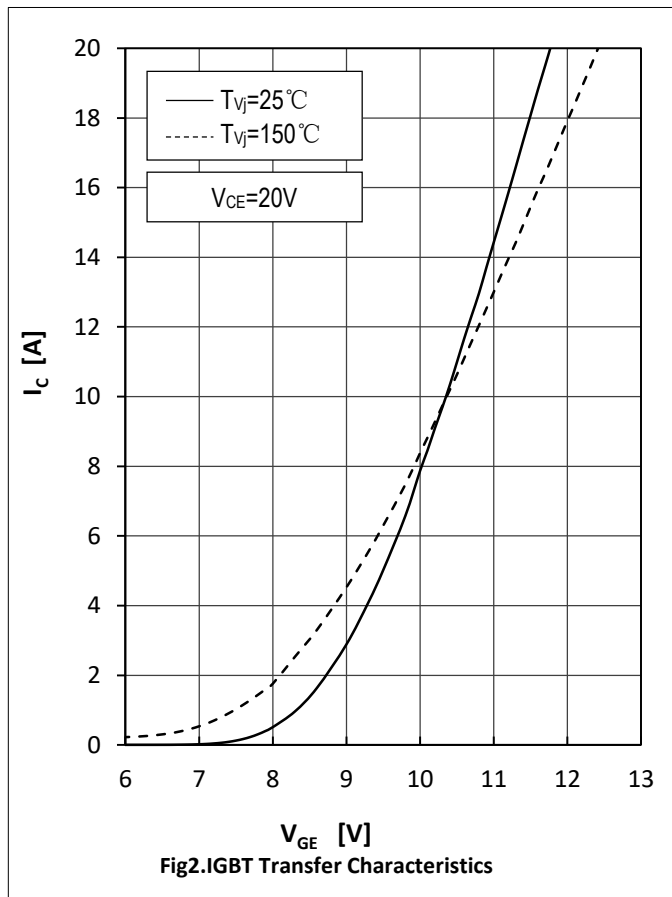
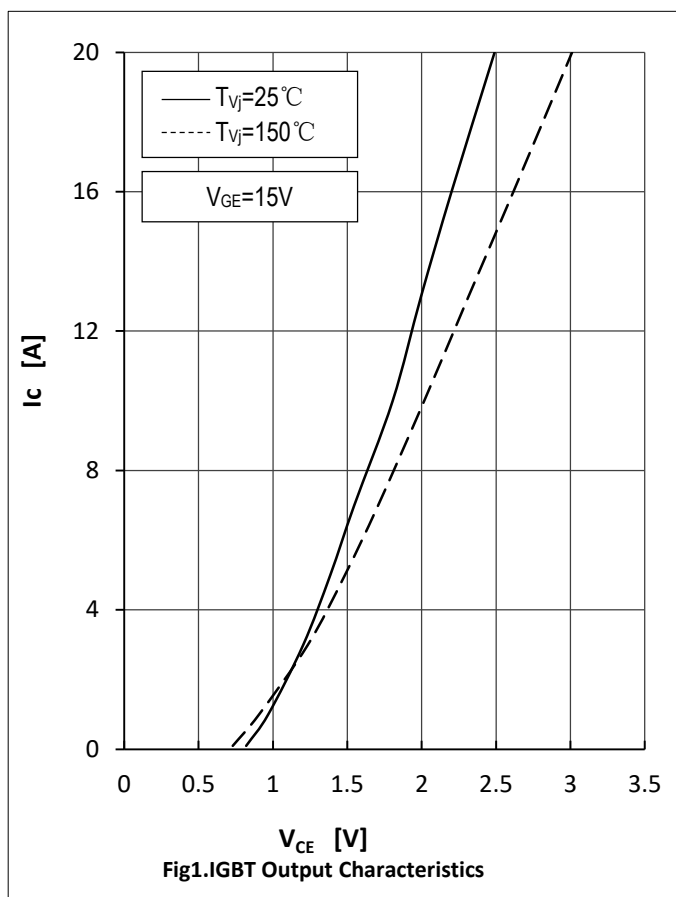
Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Rated Resistance	R_{25}			5.0		k Ω
Deviation of R100	$\Delta R/R$	$T_C=100^{\circ}\text{C}, R_{100}=493.3\Omega$	-5		5	%
Power Dissipation	P_{25}				20.0	mW
B-value	$B_{25/50}$	$R_2=R_{25}\exp[B_{25/50}(1/T_2-1/(298.15\text{K}))]$		3375		K

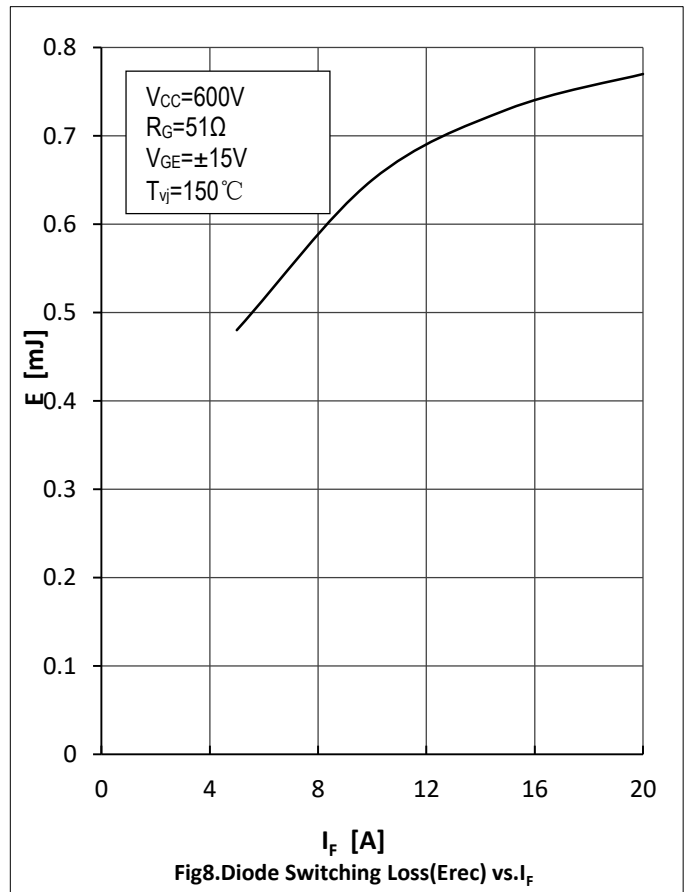
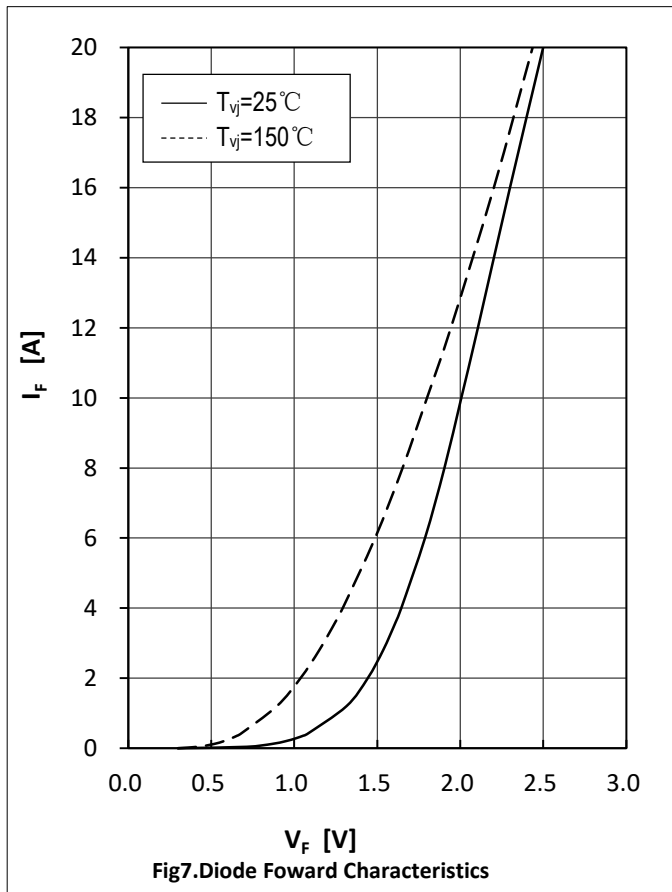
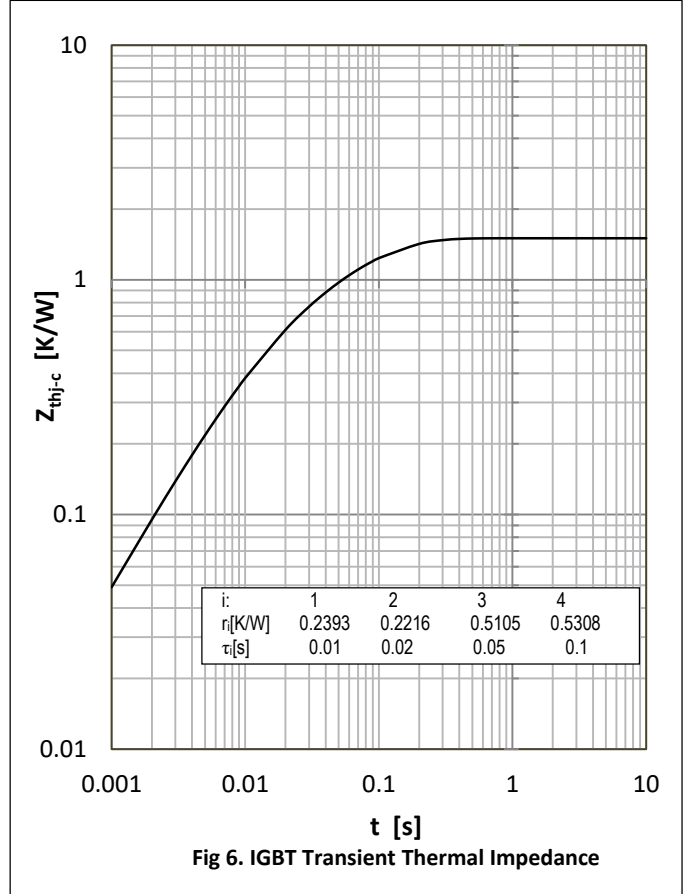
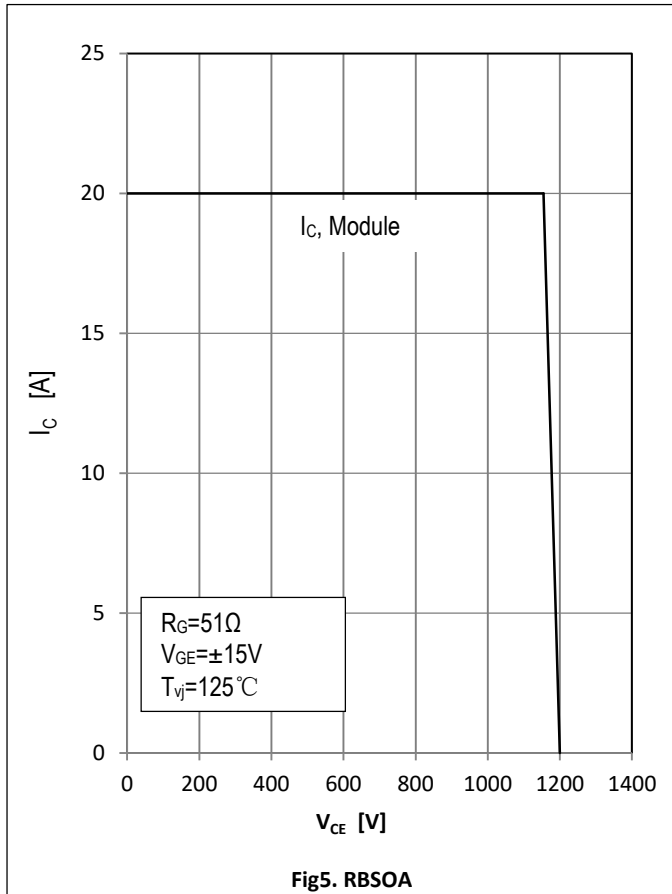


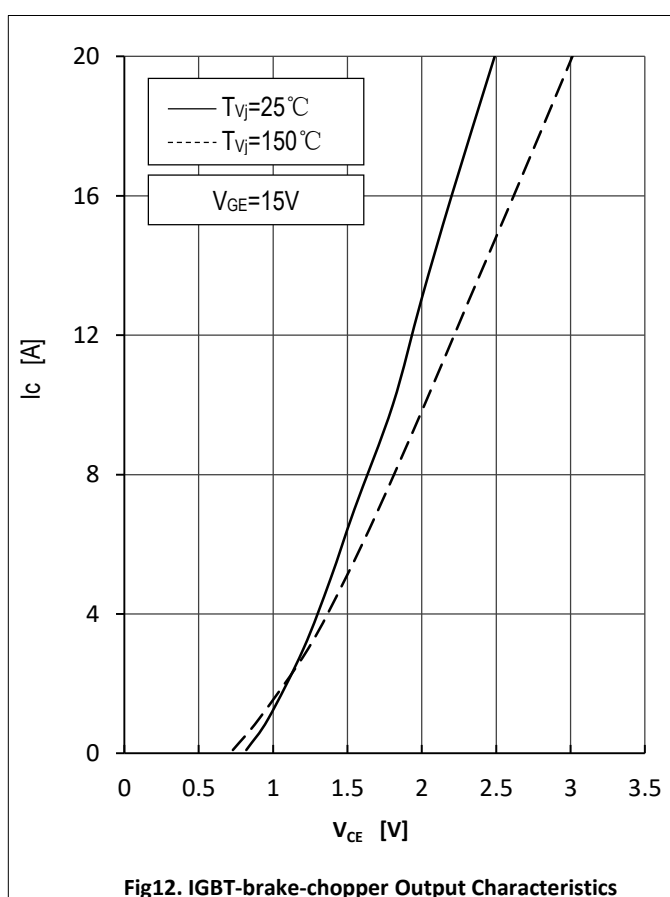
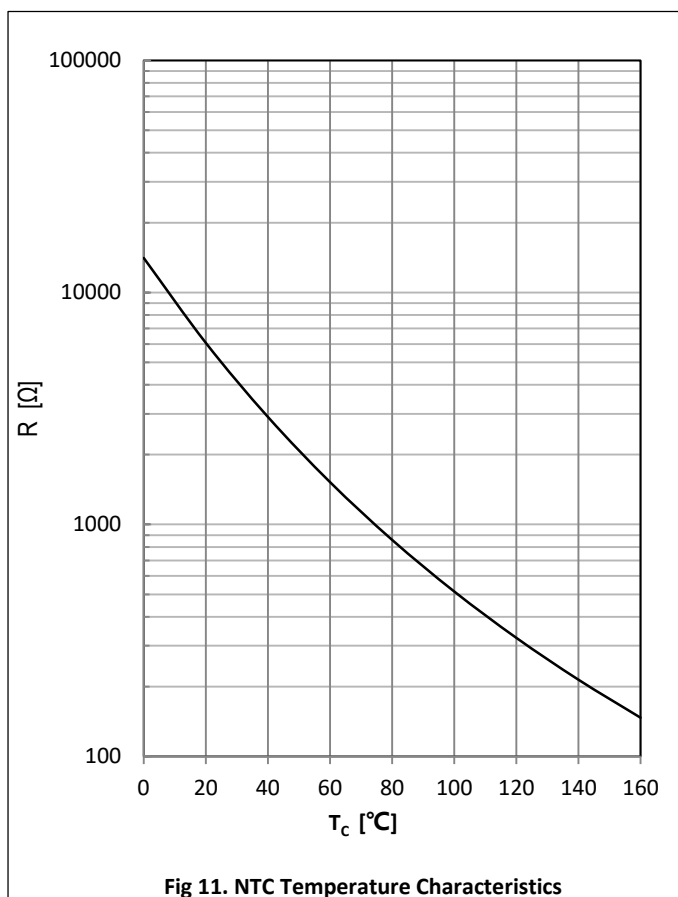
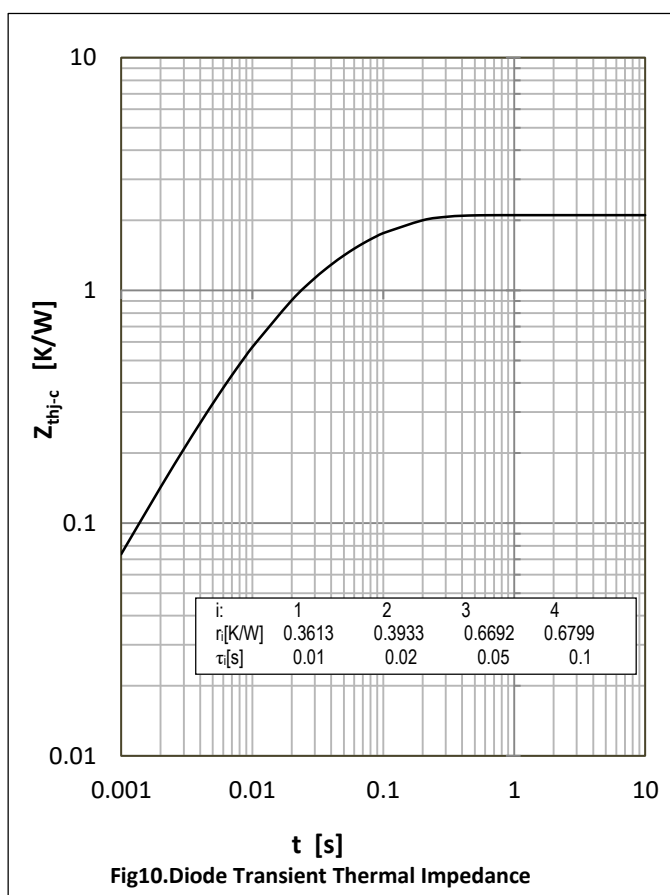
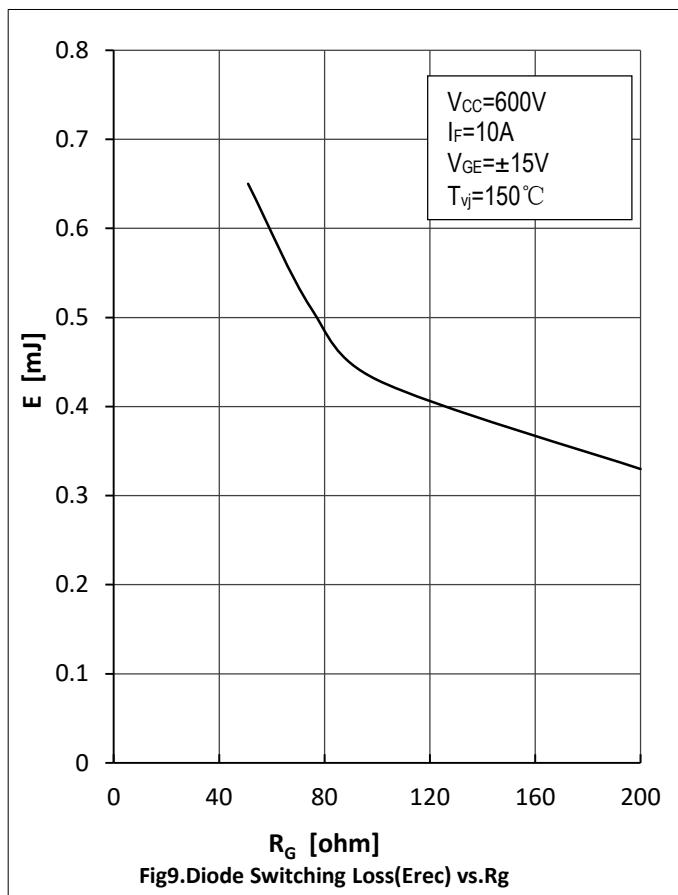
● Module Characteristics

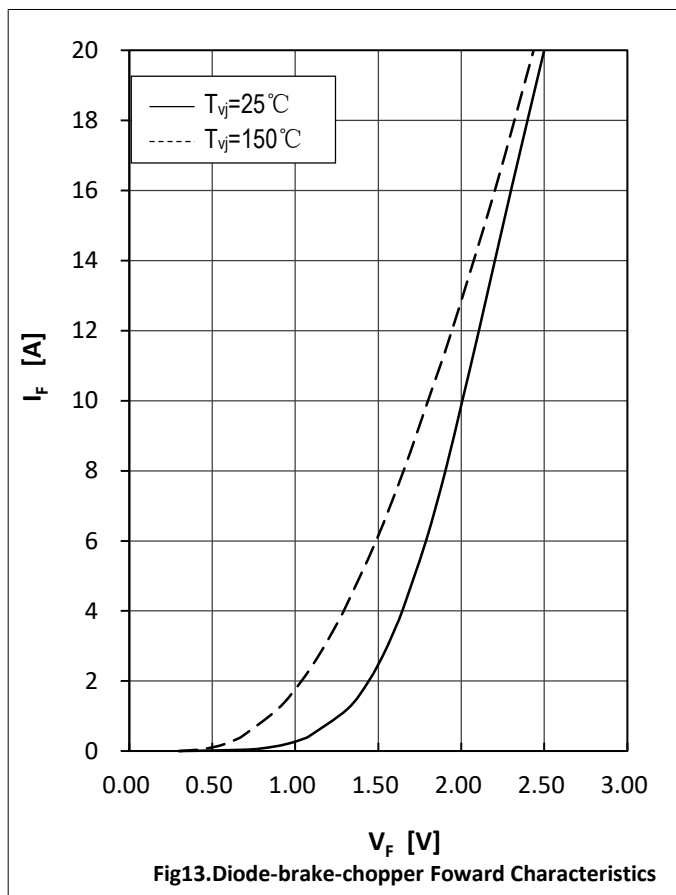
$T_c=25^{\circ}\text{C}$ unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			Min.	Typ.	Max.	
Isolation Voltage	V_{isol}	$t=1\text{min}, f=50\text{Hz}$	2500			V
Maximum Junction Temperature	T_{jmax}				175	$^{\circ}\text{C}$
Operating Junction Temperature	$T_{\text{vj op}}$		-40		150	$^{\circ}\text{C}$
Storage Temperature	T_{stg}		-40		125	$^{\circ}\text{C}$
Stray-inductance-module	L_{SCE}			30		nH
Module lead resistance, terminals-chip	$R_{\text{CC}'+\text{EE}'}$	$T_c=25^{\circ}\text{C}$, per switch		8.00		m Ω
	$R_{\text{AA}'+\text{CC}'}$			6.00		
Thermal Resistance Junction-to-Case	$R_{\theta\text{JC}}$	per IGBT-inverter			1.5	K/W
		per Diode-inverter			2.1	
		per IGBT-brake-chopper			1.5	
		per Diode-chopper			2.1	
		per Diode-rectifier			1.45	
Thermal Resistance Case-to-Sink	$R_{\theta\text{CS}}$	per IGBT-inverter		1.15		K/W
		per Diode-inverter		1.30		
		per IGBT-brake-chopper		1.15		
		per Diode-chopper		1.30		
		per Diode-rectifier		1.25		
		per Module		0.058		
Mounting Force Per Clamp	F		20		50	N
Weight of Module	G			25		g

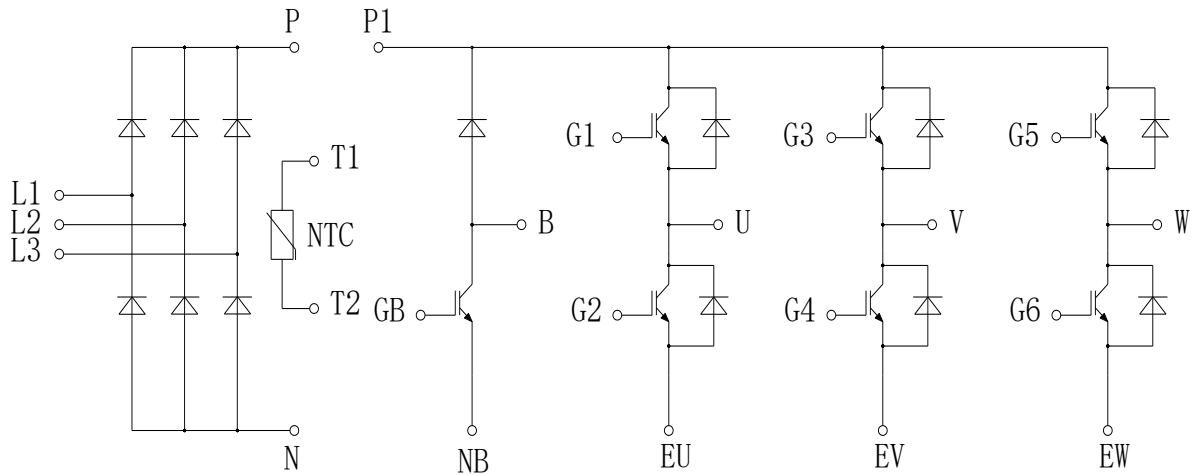




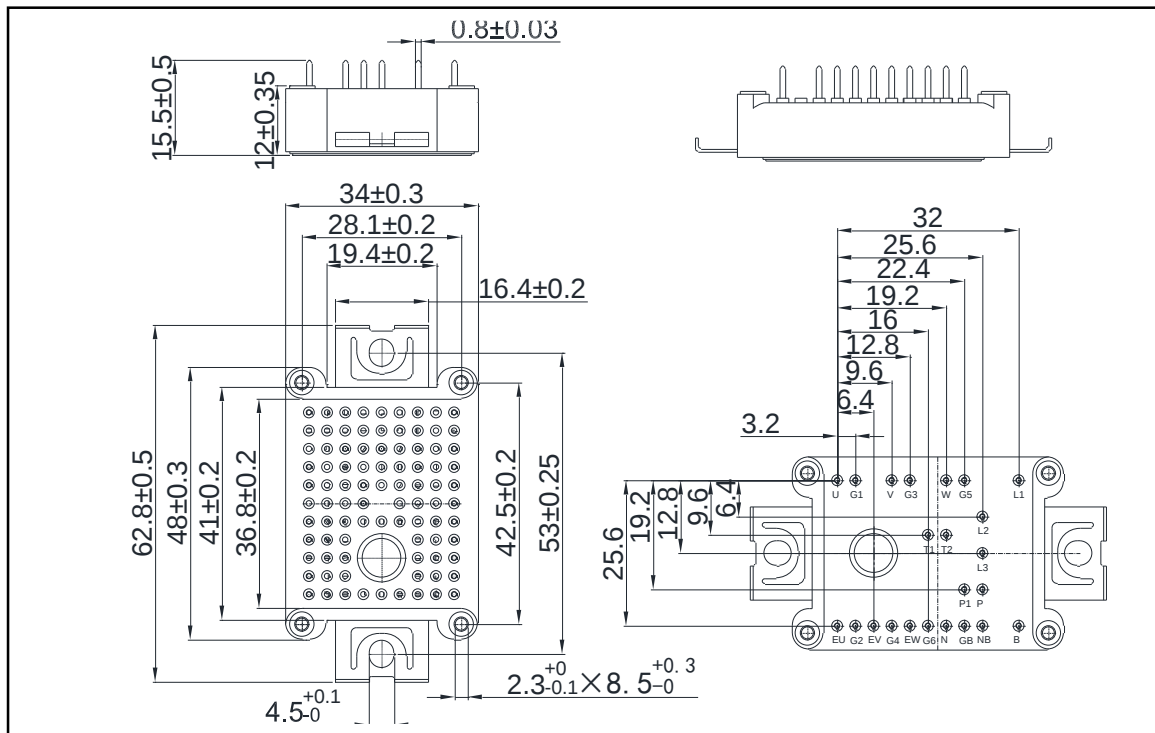




Circuit Diagram



Package Dimensions





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IGBTs is the device which is sensitive to the static electricity, it is necessary to protect the device from being damaged by the static electricity when using it.

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